



DMNH6042SPS

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
60V	50mΩ @ V _{GS} = 10V	24A		
	$65m\Omega @ V_{GS} = 4.5V$	21A		

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

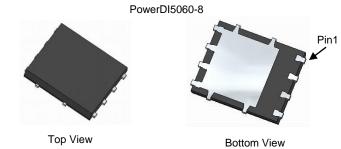
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

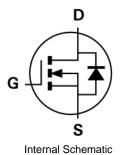
Features and Benefits

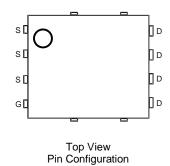
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_q Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMNH6042SPSQ</u>)

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)







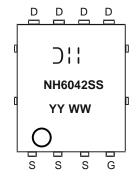
Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6042SPS-13	PowerDI5060-8	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking
NH6042SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 7) $V_{GS} = 10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +100^{\circ}C$			I _D	24 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	35	Α		
Maximum Continuous Body Diode Forward Current	Is	24	Α		
Avalanche Current (Note 8) L = 10mH			I _{AS}	3.5	Α
Avalanche Energy (Note 8) L = 10mH			E _{AS}	65	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

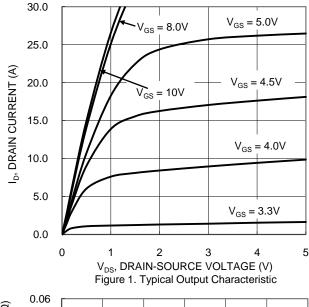
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	1.5	W
Thermal Pagistance, Junation to Ambient (Note 5)	Steady state	Б	98	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	54	
Total Power Dissipation (Note 6)		P _D	2.9	W
Thermal Decistores, Junction to Ambient (Note 6)	Steady state	Б	51	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	3.5		
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

	Symbol						
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage		60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C		_	_	1	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	_	45	65		$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	584	_	pF)/ O5)/)/ O)/	
Output Capacitance	Coss	_	83	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	24	_	pF	1 = 1.0WH 12	
Gate Resistance	R_g	_	3.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	4.2	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	8.8	_	nC	V _{DS} = 44V. I _D = 5.2A	
Gate-Source Charge	Q_{gs}	_	1.8	_	nC	$V_{DS} = 44V, I_D = 5.2A$	
Gate-Drain Charge	Q_{gd}	_	1.8	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 1A$	
Turn-On Rise Time	t_R	_	1.9	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	10.1	_	ns		
Turn-Off Fall Time	t _F	_	4.5	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	12.9	_	ns	I _F = 2.6A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	5.4	_	nC	$I_F = 2.6A$, $di/dt = 100A/\mu s$	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C. 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





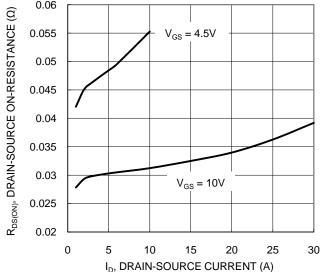


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

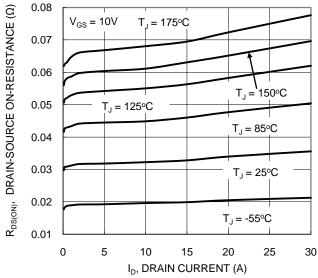
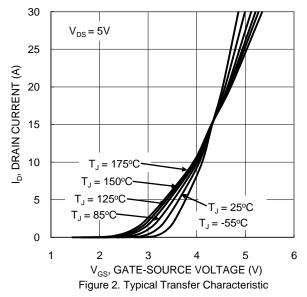
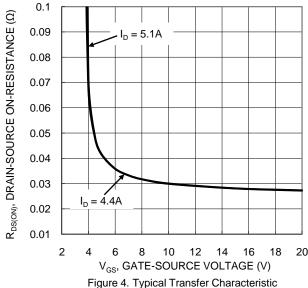


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



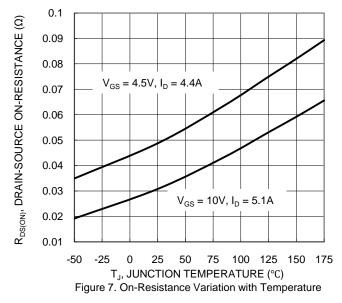


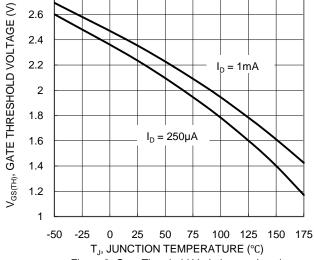
2.4 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2.2 $V_{GS} = 10V, I_D = 5.1A$ 2 1.8 1.6 1.4 1.2 $V_{GS} = 4.5V, I_{D} = 4.4A$ 1 8.0 0.6 0.4 50 75 100 125 150 175 -50 -25 0 25 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



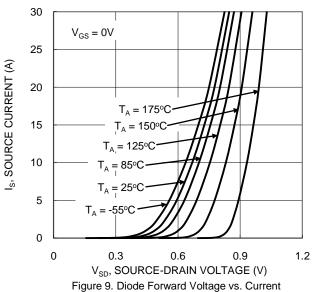


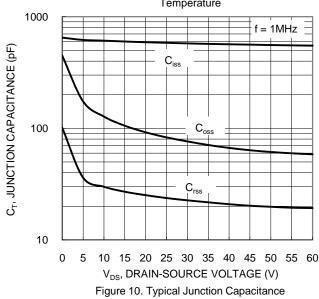


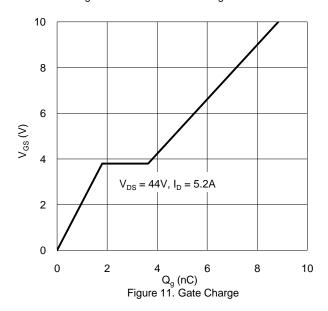


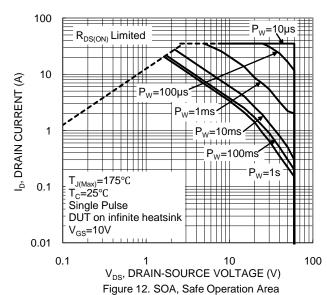
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Figure 8. Gate Threshold Variation vs. Junction Temperature

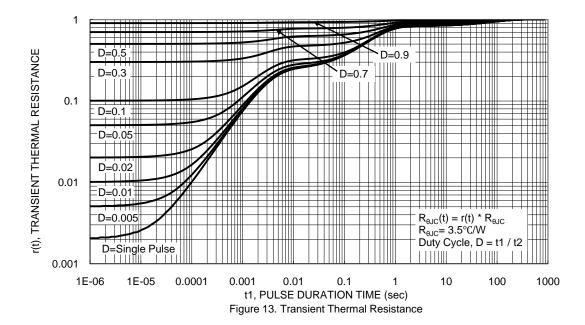










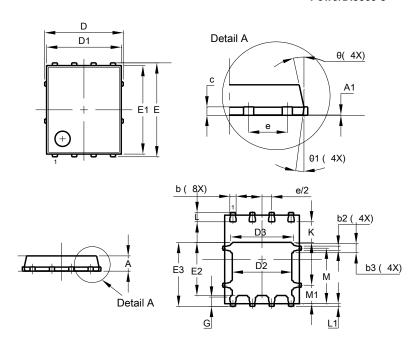




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

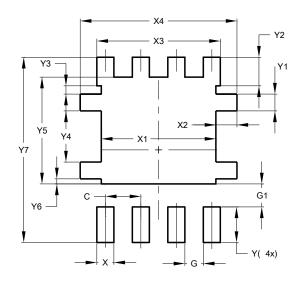


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е		6.15 BSC	•		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	_	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6°	8º	7º		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
Х	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Υ	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				



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